



70V NPN LOW SATURATION TRANSISTOR IN SOT-666

Features

- BVceo = 70V, BVcbo = 150V
- Ic Cont. 2A
- 5A Peak Pulse Current
- Extremely Low Equivalent On Resistance; $R_{CE(sat)} = 130 \text{m}\Omega$ at
- Lead, Halogen, and Antimony Free/RoHS Compliant (Note 1)
- "Green" Devices (Note 2)

Mechanical Data

- Case: SOT-666
- Case material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.003 grams (Approximate)

Applications

DC-DC converter



Top View



Device Schematic



Pin Out Configuration

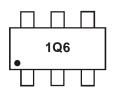
Ordering Information (Note 3)

- 1					
ĺ	Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
	ZXTN26070CV-7	1Q6	7	8mm	3000

Notes:

- 1. No purposefully added lead. Halogen and Antimony free: <900ppm bromine, <900ppm chlorine (<1500ppm total) and <1000ppm antimony compounds.
- Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com
 For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



1Q6 = Product Type Marking Code





Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	150	V
Collector-Emitter Voltage	V _{CEO}	70	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	2	Α
Peak Pulse Current	I _{CM}	5	Α
Base Current	Ι _Β	500	Α

Thermal Characteristics

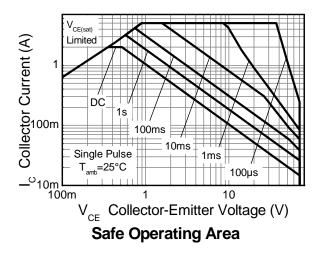
Characteristic	Symbol	Value	Unit
Power Dissipation at T _A = 25°C (Note 4)	P_{D}	0.6	W
Power Dissipation at T _A = 25°C (Note 5)	P _D	1	W
Thermal Resistance, Junction to Ambient (Note 4) @ T _A = 25°C	$R_{ hetaJA}$	208	°C/W
Thermal Resistance, Junction to Ambient (Note 5) @ T _A = 25°C	$R_{ heta JA}$	121	°C/W
Thermal Resistance, Junction to Lead (Note 6)	$R_{ heta JL}$	37	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

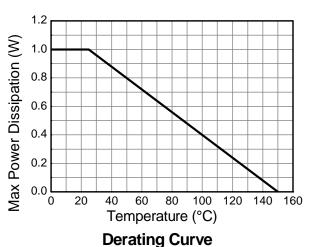
Notes:

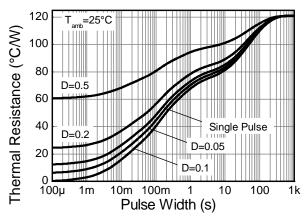
- 4. For a device surface mounted minimum recommended pad layout, in still air conditions 5. Mounted on 25mm X 25mm X 1.6mm FR4 PCB with high coverage of single sided 2 oz copper, in still air conditions. 6. From Collector leads. Typical.

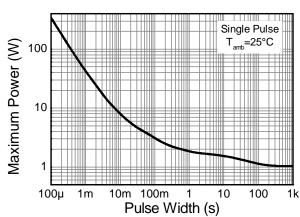


Thermal Characteristics and Derating Information









Transient Thermal Impedance

Pulse Power Dissipation





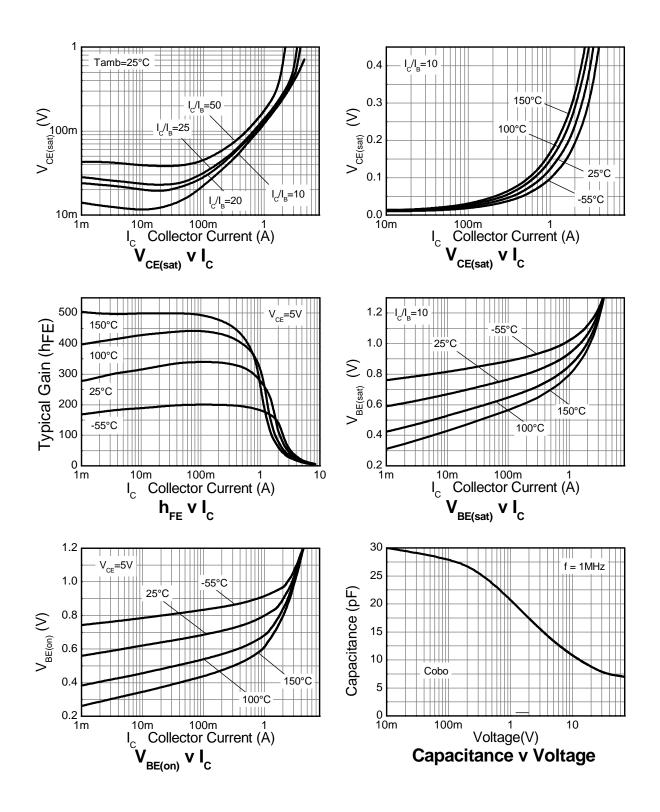
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	150	190	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 7)	V _{(BR)CEO}	70	80	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	7	8.3	_	V	I _E = 100μA
Collector Cutoff Current	I _{CBO} , I _{CES}	_	-	100	nA	V _{CB} = 60V , V _{CES} = 60V
Emitter Cutoff Current	I _{EBO}	_	-	100	nA	V _{EB} = 5.6V
ON CHARACTERISTICS (Note 7)						
DC Current Gain	h _{FE}	190 200 75	320 340 110	- - -	-	$I_{C} = 10mA$, $V_{CE} = 5V$ $I_{C} = 100mA$, $V_{CE} = 5V$ $I_{C} = 2A$, $V_{CE} = 5V$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	- - - -	22 110 147 135 265	30 150 200 165 330	V	$I_C = 0.1A, I_B = 10mA$ $I_C = 0.5A, I_B = 10mA$ $I_C = 1A, I_B = 50mA$ $I_C = 1A, I_B = 100mA$ $I_C = 2A, I_B = 200mA$
Base-Emitter Turn-On Voltage	V _{BE(ON)}	_	0.85	1.0	V	I _C = 1A, V _{CE} = 2V
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	0.90	1.1	V	I _C = 1A, I _B = 50mA
SMALL SIGNAL CHARACTERISTICS	,					
Output Capacitance	C_{obo}	_	10	_	pF	V _{CB} = 10V. f = 1MHz
Current Gain-Bandwidth Product	f _T	-	200	=	MHz	$V_{CE} = 10V, I_{C} = 50mA,$ f = 100MHz
SWITCHING CHARACTERISTICS	SWITCHING CHARACTERISTICS					
Turn-On Time	t _{on}	-	46	_	ns	$V_{CE} = 10V, I_{C} = 0.5A$
Turn-Off Time	t _{off}	_	722	_	ns	$I_{B1} = -I_{B2} = 25mA$

Notes: 7. Measured under pulsed conditions. Pulse width = 300μ s. Duty cycle $\leq 2\%$

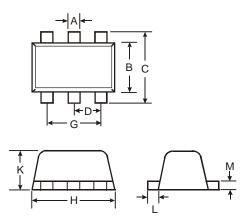


Typical Characteristics



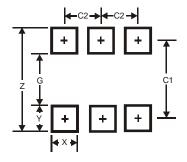


Package Outline Dimensions



SOT-666					
Dim	Min	Max	Тур		
Α	0.15	0.30	0.20		
В	1.10	1.25	1.20		
С	1.55	1.70	1.60		
D	_	_	0.50		
G	0.90	1.10	1.00		
Н	1.50	1.70	1.60		
K	0.55	0.60	0.60		
L	0.10	0.30	0.20		
М	0.10	0.18	0.15		
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Υ	0.5
C1	1.7
C2	0.5





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